

High Efficiency LED, ø 3 mm Tinted Total Diffused

Color	Type	Technology	Angle of Half Intensity $\pm\varphi$
High efficiency red	TLHR46..	GaAsP on GaP	60°
Yellow	TLHY46..	GaAsP on GaP	60°
Green	TLHG46..	GaP on GaP	60°

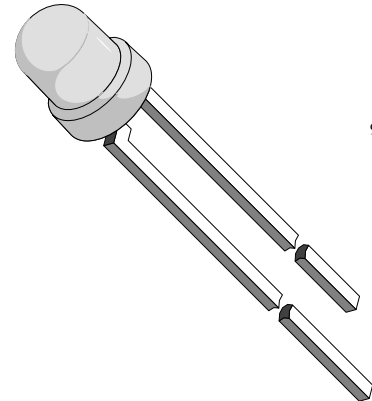
Description

The TLH.46.. series was developed for applications which need a very wide radiation angle like back-lighting, general indicating and lighting purposes.

It is housed in a 3 mm tinted total diffused plastic package. The wide viewing angle of these devices provides a high on-off contrast.

Several selection types with different luminous intensities are offered. All LEDs are categorized in luminous intensity groups. The green and yellow LEDs are categorized additionally in wavelength groups.

That allows users to assemble LEDs with uniform appearance.



94 8488

Features

- Choice of three bright colors
- Standard T-1 package
- Small mechanical tolerances
- Suitable for DC and high peak current
- Very wide viewing angle
- Luminous intensity categorized
- Yellow and green color categorized

Applications

Status lights
OFF / ON indicator
Background illumination
Readout lights
Maintenance lights
Legend light

Absolute Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

TLHR46.. , TLHY46.. , TLHG46.. ,

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	6	V
DC forward current	$T_{amb} \leq 60^{\circ}\text{C}$	I_F	30	mA
Surge forward current	$t_p \leq 10 \mu\text{s}$	I_{FSM}	1	A
Power dissipation	$T_{amb} \leq 60^{\circ}\text{C}$	P_V	100	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$
Operating temperature range		T_{amb}	-20 to +100	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55 to +100	$^{\circ}\text{C}$
Soldering temperature	$t \leq 5 \text{ s}$, 2 mm from body	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction/ambient		R_{thJA}	400	K/W

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

High efficiency red (TLHR46..)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity ¹⁾	I _F = 10 mA	TLHR4600	I _V	1	2		mcd
		TLHR4601	I _V	1.6	3.5		mcd
		TLHR4605	I _V	2.5	6		mcd
Dominant wavelength	I _F = 10 mA		λ _d	612		625	nm
Peak wavelength	I _F = 10 mA		λ _p		635		nm
Angle of half intensity	I _F = 10 mA		φ		±60		deg
Forward voltage	I _F = 20 mA		V _F		2	3	V
Reverse voltage	I _R = 10 μA		V _R	6	15		V
Junction capacitance	V _R = 0, f = 1 MHz		C _j		50		pF

¹⁾ in one Packing Unit I_VMin./ I_V Max. ≤ 0.5

Yellow (TLHY46..)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity ¹⁾	I _F = 10 mA	TLHY4600	I _V	0.63	2		mcd
		TLHY4601	I _V	1	3.5		mcd
		TLHY4605	I _V	2.5	5		mcd
Dominant wavelength	I _F = 10 mA		λ _d	581		594	nm
Peak wavelength	I _F = 10 mA		λ _p		585		nm
Angle of half intensity	I _F = 10 mA		φ		±60		deg
Forward voltage	I _F = 20 mA		V _F		2.4	3	V
Reverse voltage	I _R = 10 μA		V _R	6	15		V
Junction capacitance	V _R = 0, f = 1 MHz		C _j		50		pF

¹⁾ in one Packing Unit I_VMin./ I_V Max. ≤ 0.5

Green (TLHG46..)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity ¹⁾	I _F = 10 mA	TLHG4600	I _V	1	2		mcd
		TLHG4601	I _V	1.6	3.5		mcd
		TLHG4605	I _V	4	6		mcd
Dominant wavelength	I _F = 10 mA		λ _d	562		575	nm
Peak wavelength	I _F = 10 mA		λ _p		565		nm
Angle of half intensity	I _F = 10 mA		φ		±60		deg
Forward voltage	I _F = 20 mA		V _F		2.4	3	V
Reverse voltage	I _R = 10 μA		V _R	6	15		V
Junction capacitance	V _R = 0, f = 1 MHz		C _j		50		pF

¹⁾ in one Packing Unit I_VMin./ I_V Max. ≤ 0.5

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

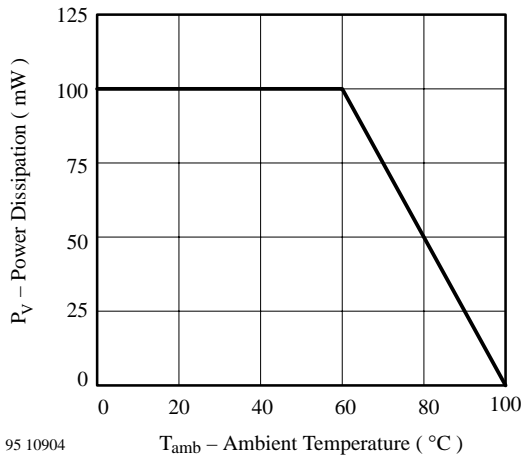


Figure 1. Power Dissipation vs. Ambient Temperature

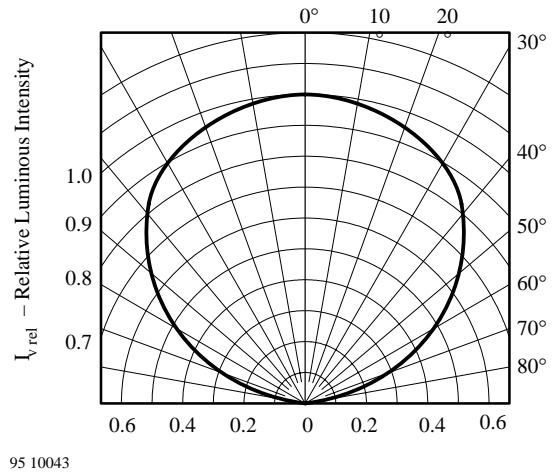


Figure 4. Rel. Luminous Intensity vs. Angular Displacement

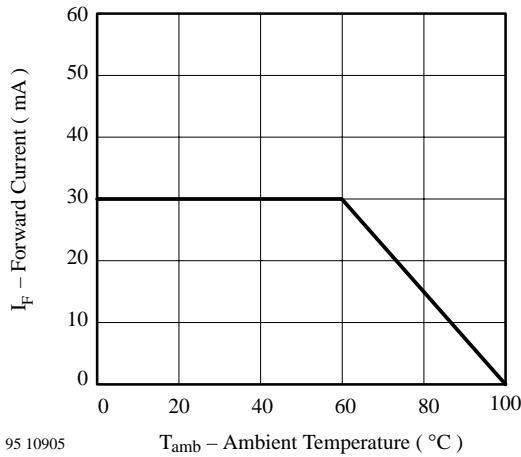


Figure 2. Forward Current vs. Ambient Temperature

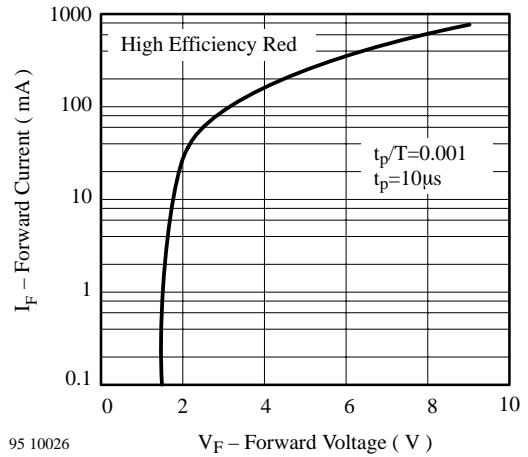


Figure 5. Forward Current vs. Forward Voltage

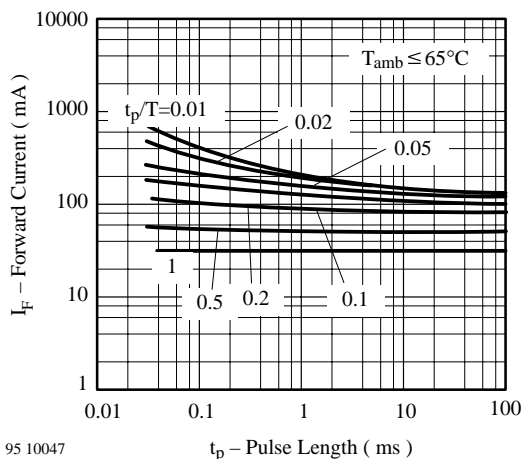


Figure 3. Forward Current vs. Pulse Length

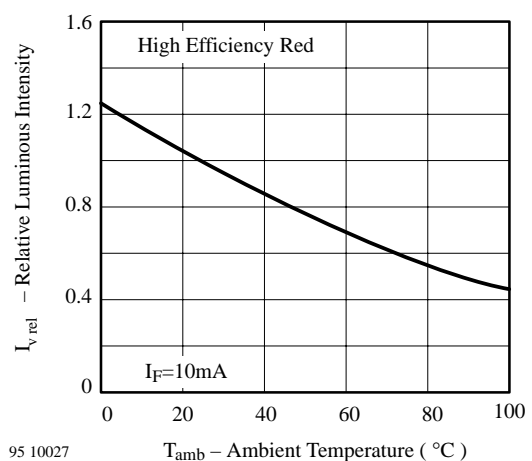


Figure 6. Rel. Luminous Intensity vs. Ambient Temperature

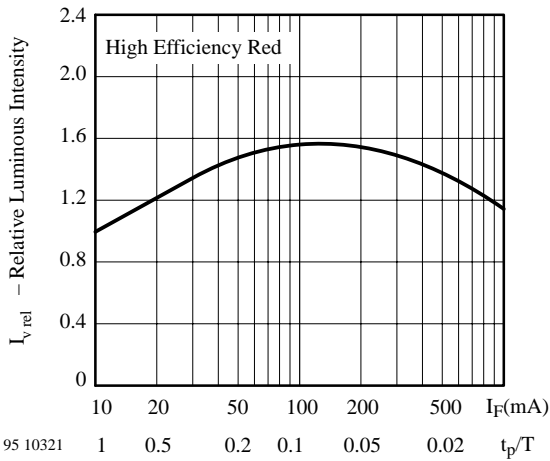


Figure 7. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

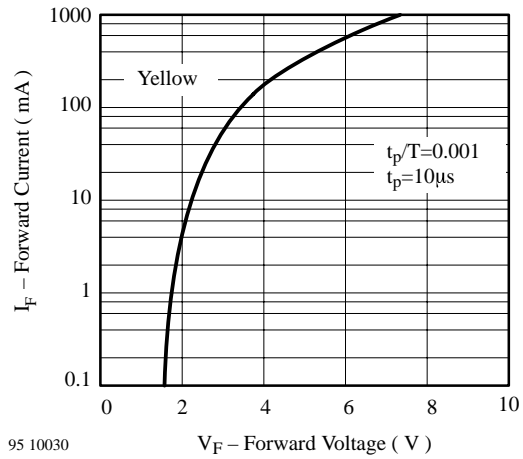


Figure 10. Forward Current vs. Forward Voltage

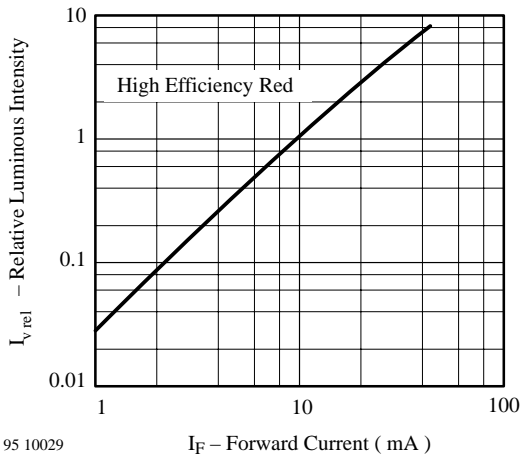


Figure 8. Relative Luminous Intensity vs. Forward Current

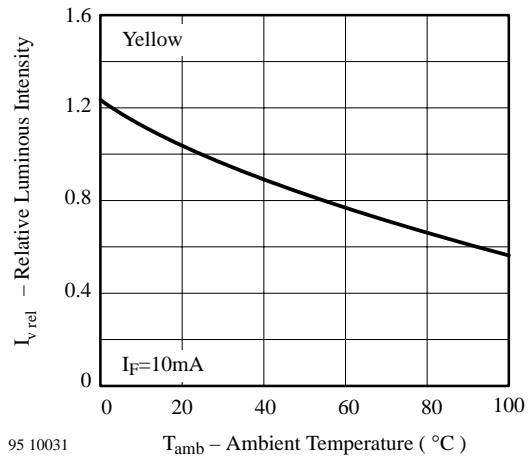


Figure 11. Rel. Luminous Intensity vs. Ambient Temperature

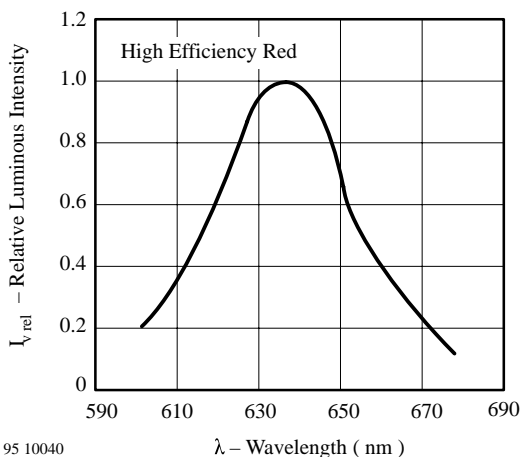


Figure 9. Relative Luminous Intensity vs. Wavelength

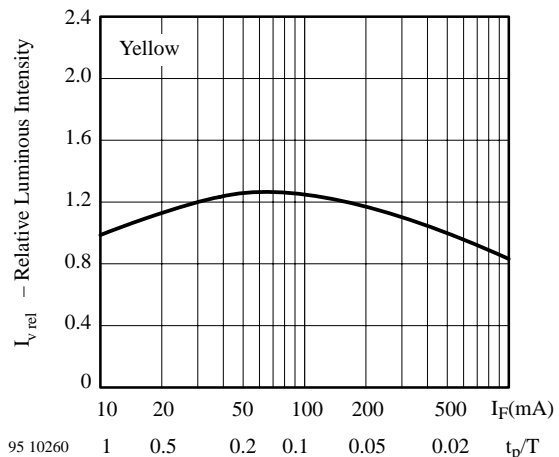


Figure 12. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

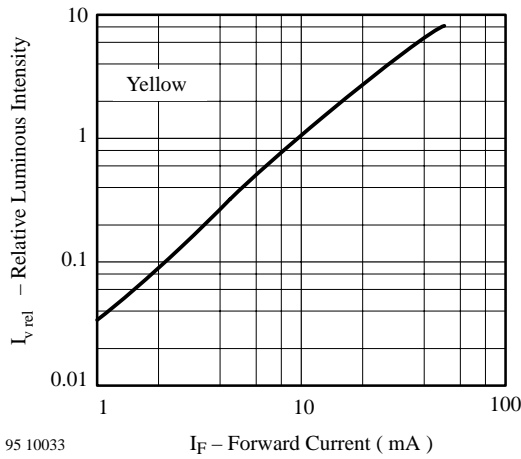


Figure 13. Relative Luminous Intensity vs. Forward Current

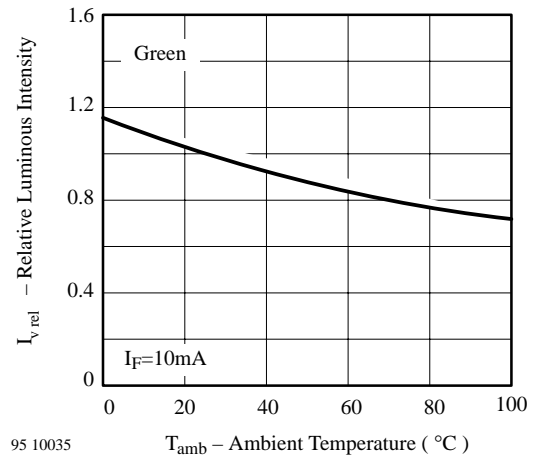


Figure 16. Rel. Luminous Intensity vs. Ambient Temperature

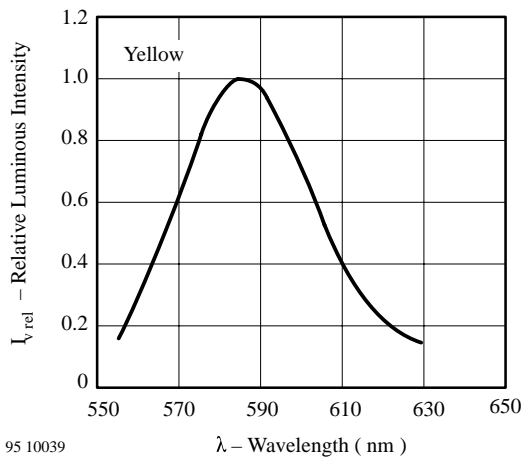


Figure 14. Relative Luminous Intensity vs. Wavelength

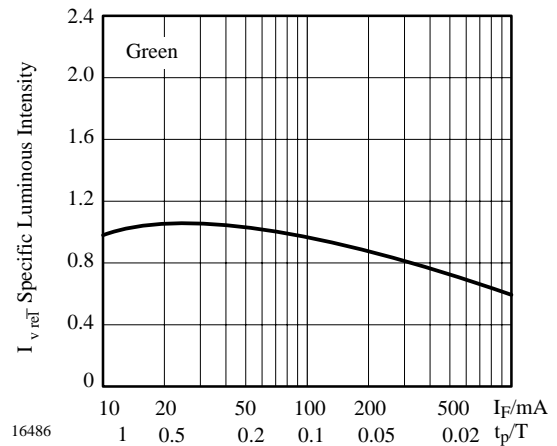


Figure 17. Specific Luminous Intensity vs. Forward Current

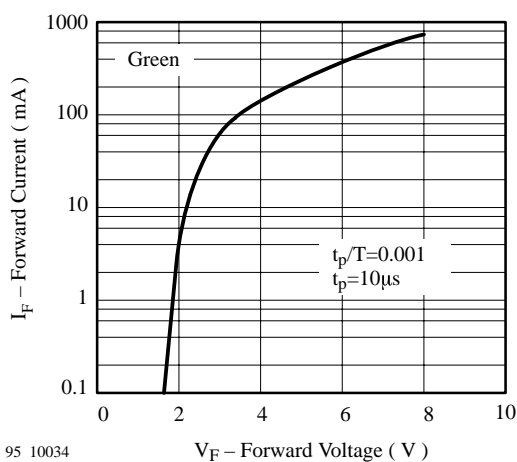


Figure 15. Rel. Luminous Intensity vs. Ambient Temperature

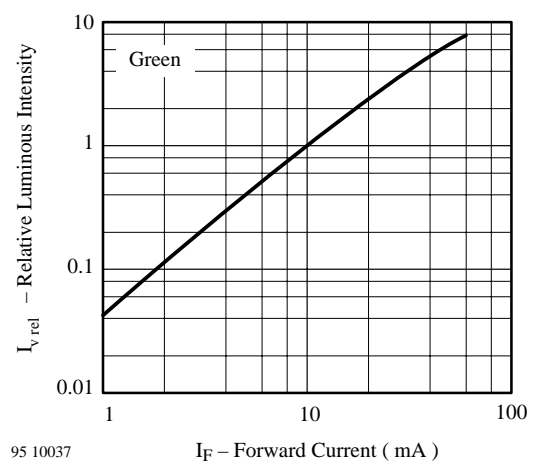


Figure 18. Relative Luminous Intensity vs. Forward Current

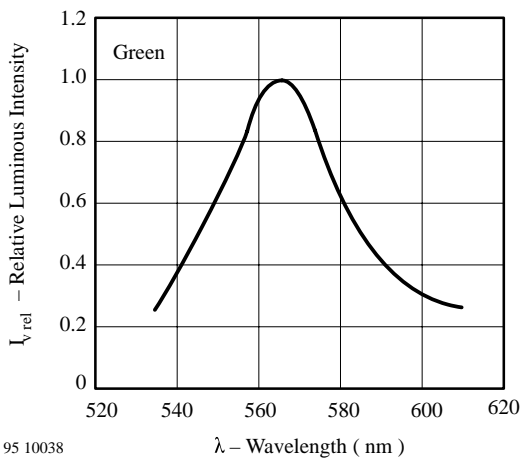
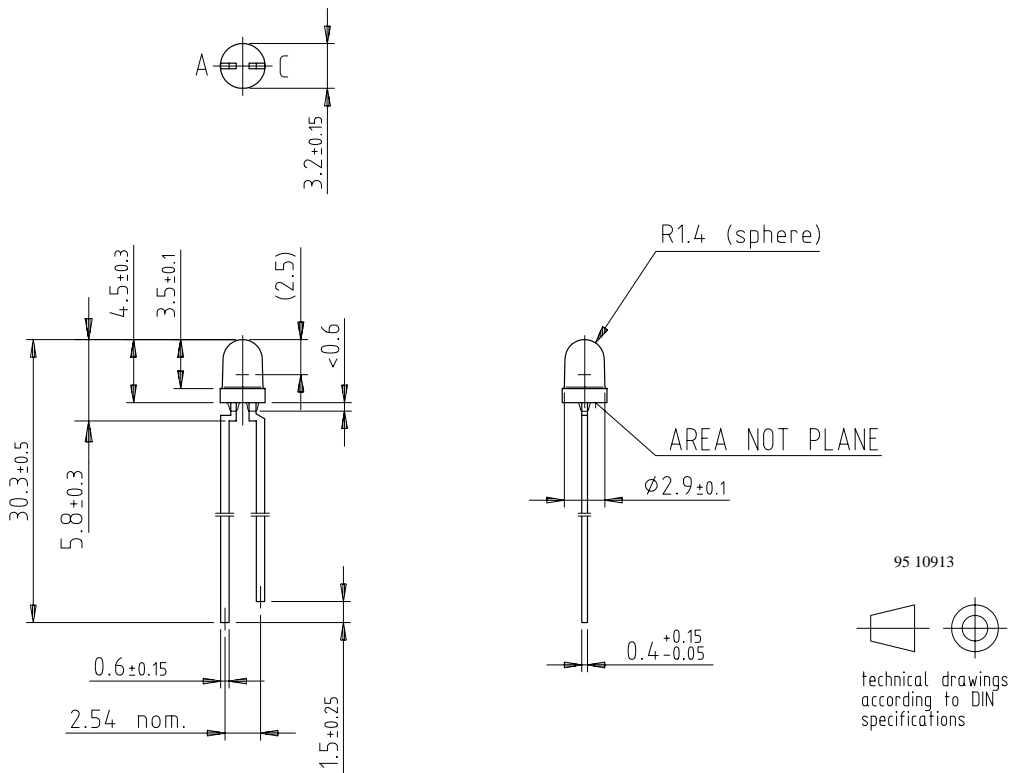


Figure 19. Relative Luminous Intensity vs. Wavelength

Dimensions in mm





Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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